

DMS3012SFG

## **Marking Information**



N12 = Product Type Marking Code YYWW = Date Code Marking YY = Last Two Digits of Year (ex: 18 = 2018) WW = Week Code (01 to 53)

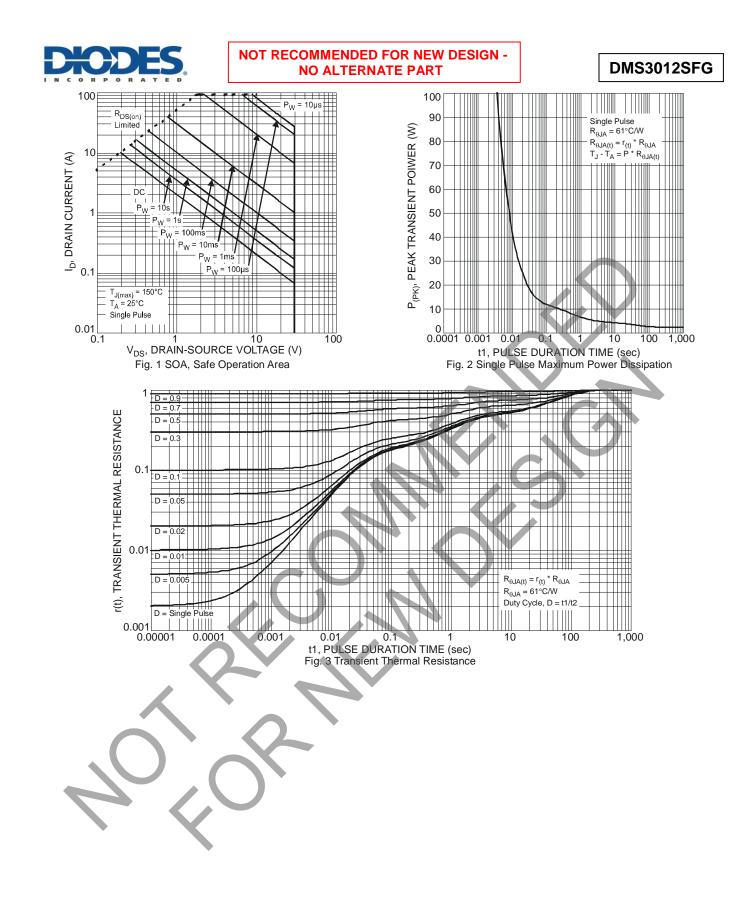
## **Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic Drain-Source Voltage			Symbol	Value	Unit V
			V <sub>DSS</sub>	30	
Gate-Source Voltage			V <sub>GSS</sub>	±20	V
	Steady State	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	Чр	12 9.5	A
Continuous Drain Current (Note 6) $V_{GS} = 10V$	t < 10s	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	ID	16.0 12.7	А
	Steady State	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	lp	9.5 7.5	A
Continuous Drain Current (Note 6) $V_{GS} = 4.5V$	t < 10s	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	Ι <sub>D</sub>	13.0 10.3	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	)		IDM	90	A
Maximum Continuous Body Diode Forward Current (	(Note 6)		1 <sub>S</sub>	3.5	A
Avalanche Current (Note 7) L = 0.1mH			I <sub>AS</sub>	17	A
Avalanche Energy (Note 7) L = 0.1mH			EAS	43	mJ

## **Thermal Characteristics**

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T <sub>A</sub> = +25°C		0.89	W
Total Power Dissipation (Note 5)	T <sub>A</sub> = +70°C	PD	0.55	
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	D	145	°C/W
Thermal Resistance, Sunction to Ambient (Note 5)	t < 10s	$R_{ heta}$ JA	74	
Total Power Dissipation (Note 6)	$T_A = +25^{\circ}C$	Р	2.2	W
Total Power Dissipation (Note 6)	T <sub>A</sub> = +70°C	PD	1.3	
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	D	58	°C/W
Thermal Resistance, Junction to Ambient (Note 6)	t < 10s	$R_{ heta JA}$	31	
Thermal Resistance, Junction to Case (Note 6)		$R_{ ext{ heta}JC}$	11	
Operating and Storage Temperature Range		T <sub>J,</sub> T <sub>STG</sub>	-55 to +150	°C

5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout. 6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate. 7.  $I_{AS}$  and  $E_{AS}$  ratings are based on low frequency and duty cycles to keep  $T_J = +25^{\circ}$ C. Notes:

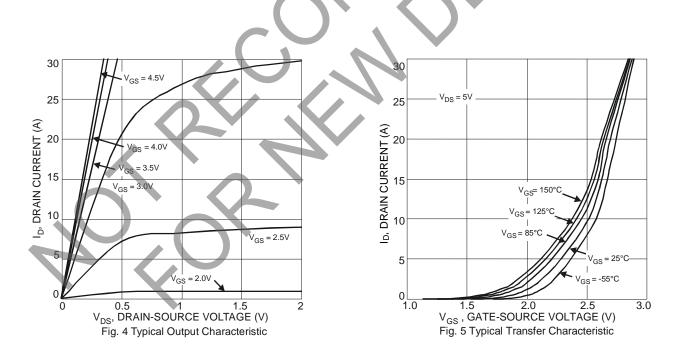




# **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						•
Drain-Source Breakdown Voltage	<b>BV</b> <sub>DSS</sub>	30	—	_	V	$V_{GS} = 0V, I_D = 250 \mu A$
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	—	—	100	μA	$V_{DS} = 30V, V_{GS} = 0V$
Gate-Source Leakage	Igss		_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 8)						·
Gate Threshold Voltage	V <sub>GS(TH)</sub>	1.0	1.5	2.5	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$
Static Drain-Source On-Resistance	D D	—	7.3	10	- mO	V <sub>GS</sub> = 10V, I <sub>D</sub> = 13.5A
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	—	10	15		V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 11A
Forward Transfer Admittance	Y <sub>fs</sub>	_	30	_	S	V <sub>DS</sub> = 5V, I <sub>D</sub> = 10.0A
Diode Forward Voltage	V <sub>SD</sub>		0.45	0.55	V	$V_{GS} = 0V, I_S = 1A$
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C <sub>iss</sub>		1296	4310	pF	
Output Capacitance	Coss		415	_	pF	$V_{DS} = 15V, V_{GS} = 0V,$ f = 1.0MHz
Reverse Transfer Capacitance	Crss	_	204	_	pF	
Gate Resistance	Rq	0.26	1.6	2.6	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$
Total Gate Charge V <sub>GS</sub> = 4.5V	Qg	—	14.7	+	nC	
Total Gate Charge V <sub>GS</sub> = 10V	Qg	_	31.6	—	nC	
Gate-Source Charge	Q <sub>gs</sub>		3.5		nC	$V_{DS} = 15V, V_{GS} = 10V, I_D = 13.5A$
Gate-Drain Charge	Q <sub>gd</sub>	—	5.0		nC	
Turn-On Delay Time	t <sub>D(on)</sub>		15.8		ns	
Turn-On Rise Time	tr		27.8		ns	$V_{GS} = 10V, V_{DS} = 15V,$
Turn-Off Delay Time	t <sub>D(off)</sub>	_	29.7	_	ns	$R_{g} = 3\Omega, I_{D} = 8.8A$
Turn-Off Fall Time	t <sub>f</sub>	ł	13.6	—	ns	1
Reverse Recovery Time	trr		13.1		ns	1 <sub>F</sub> = 13.5A, di/dt = 100A/μs
Reverse Recovery Charge	Q <sub>rr</sub>		4.3	-	nC	I <sub>F</sub> = 13.5A, di/dt = 100A/µs

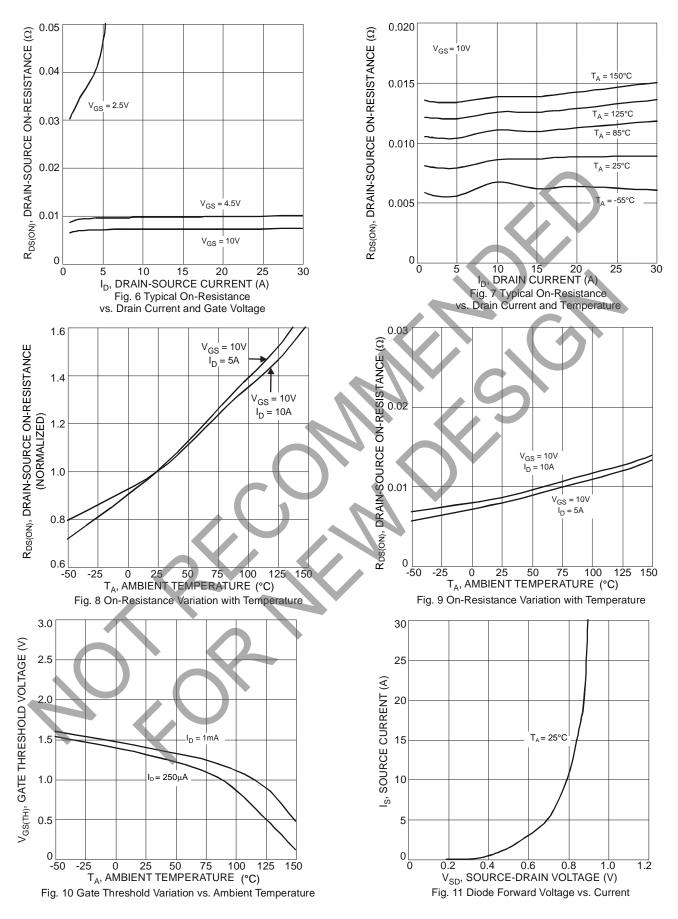
Notes: 8. Short duration pulse test used to minimize self-heating effect. 9. Guaranteed by design. Not subject to product testing.





## NOT RECOMMENDED FOR NEW DESIGN -NO ALTERNATE PART

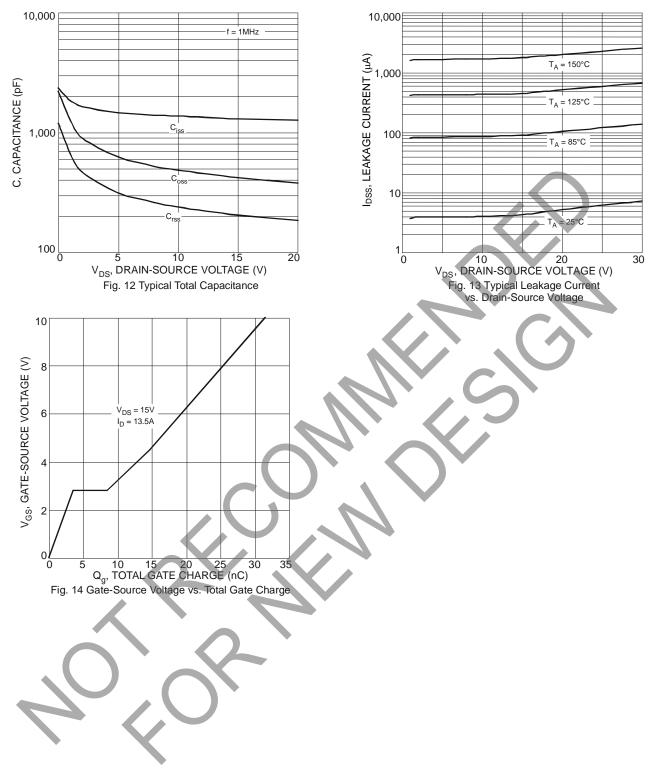
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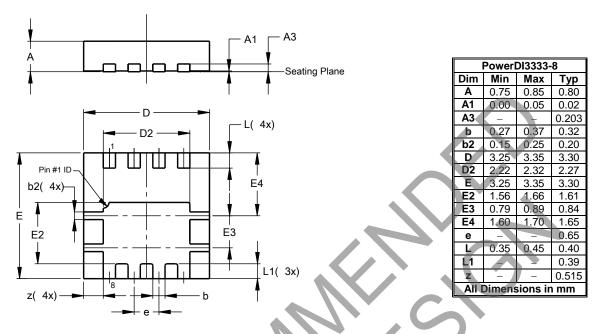
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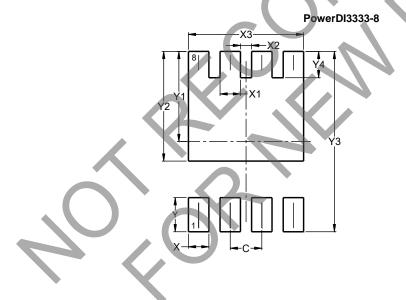
### Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.



## **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.



Dimensions	Value (in mm)
С	0.650
Х	0.420
X1	0.420
X2	0.230
X3	2.370
Y	0.700
Y1	1.850
Y2	2.250
Y3	3.700
Y4	0.540



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